

# AN11102

## BFU725F/N1 2.4 GHz LNA evaluation board

Rev. 1 — 28 July 2011

Application note

### Document information

| Info            | Content                                                            |
|-----------------|--------------------------------------------------------------------|
| <b>Keywords</b> | LNA, 2.4GHz, BFU725F/N1                                            |
| <b>Abstract</b> | This document explains the BFU725F/N1 2.4GHz LNA evaluation Board. |



## Revision history

| Rev | Date     | Description      |
|-----|----------|------------------|
| 1   | 20110728 | Initial document |

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## 1. Introduction

The BFU725F/N1 is a wideband Silicon Germanium Amplifier transistor for high speed, low noise applications. It is designed to be used for LNA applications up to 15 GHz like GPS, Satellite radio, Cordless Phone, Wireless LAN and satellite LNB. The BFU725F/N1 comes in a SOT343F package that has 2-emitter pins to reduce emitter inductance (for maximum gain).

The BFU725F/N1 is ideal in all kind of applications where cost matters. It also gives the designer flexibility in his design work, like bias current, frequency of operation; optimize for the parameter of interest e.g. noise; gain; IP3 etc

The 2.4GHz LNA evaluation board (EVB) is designed to evaluate the performance of the BFU725F/N1 applied as a general ISM band LNA in the 2.4GHz range. In this document, the application diagram, board layout, bill of material, and some typical results are given.

Fig 1 shows the evaluation board.

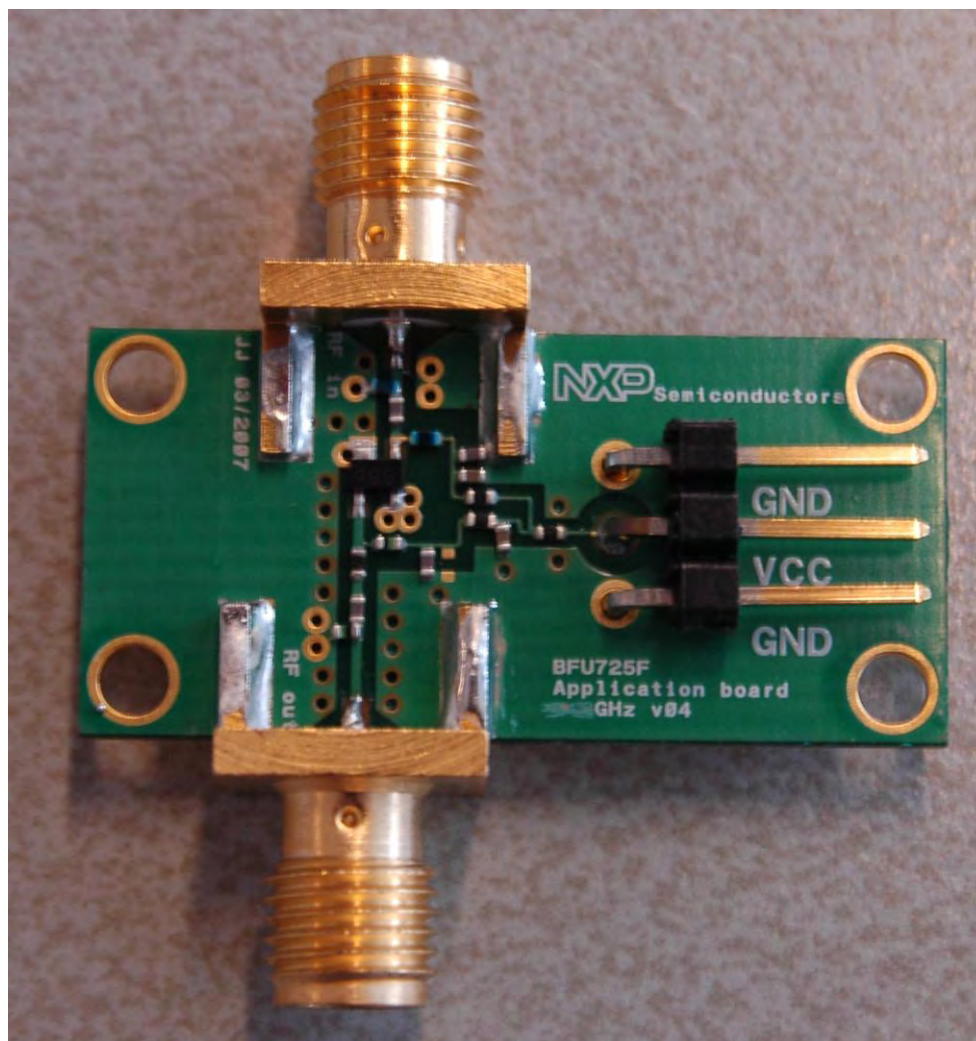


Fig 1. BFU725F/N1 2.4GHz LNA evaluation board

## 2. General description

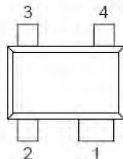
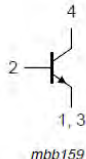
The BFU725F/N1 is the first discrete HBT produced in NXP's SiGeC QuBIC4x BiCmos process. SiGeC is a silicon germanium process with the addition of Carbon in the base layer of the NPN transistor. The presence of carbon in the base layer suppresses the boron diffusion during wafer processing that allows steeper and narrower SiGe HBT base and a heavier doped base, this results in lower base resistance, hence lower noise and higher cut off frequency (higher gain). In Table 1 a summary of the transistor performance in terms of noise and gain is shown.

**Table 1. BFU725F/N1 figures**

*Measured at 2V Vce and 5mA Ic*

| Frequency | Noise Figure | Associated gain |
|-----------|--------------|-----------------|
| 1.5 GHz   | 0.42(dB)     | 24(dB)          |
| 1.8 GHz   | 0.43(dB)     | 22(dB)          |
| 2.4 GHz   | 0.47(dB)     | 20(dB)          |
| 5.8 GHz   | 0.7(dB)      | 13.5(dB)        |
| 12 GHz    | 1.1(dB)      | 10(dB)          |

**Table 2. Pinning information of the BFU725F/N1**

| Pin | Description | Simplified outline                                                                   | Graphic symbol                                                                        |
|-----|-------------|--------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|
| 1   | Emitter     |  |  |
| 2   | Base        |                                                                                      |                                                                                       |
| 3   | Emitter     |                                                                                      |                                                                                       |
| 4   | Collector   |                                                                                      |                                                                                       |

## 3. Application Board

The BFU725F/N1 2.4GHz EVB simplifies the evaluation of the BFU725F/N1 wideband transistor, for this frequency range. The EVB enables testing of the device performance and requires no additional support circuitry. The board is fully assembled with BFU725F/N1, including input- and output matching, to optimize the performance. For input matching a compromise has to be made for optimum noise/maximum gain/RL/usable bandwidth on the application and customer requirements. To prevent unwanted oscillations the stability factor (K) must be greater than 1. The stability factor can be increased at the cost of gain. The board is mounted with signal input and output SMA connectors for connection to RF test equipment.

**Table 3. Design goals**

| Parameter          | Symbol | BFU725F/N1 EVB | Unit |
|--------------------|--------|----------------|------|
| Noise Figure       | NF     | <1             | dB   |
| Power Gain         | Gp     | >15            | dB   |
| Input Return Loss  | IRL    | >5             | dB   |
| Output Return Loss | ORL    | >5             | dB   |
| Stability factor   | K      | >1             | -    |

3.1 Application Circuit

In Fig 2 the application diagram as supplied on the evaluation board is given.

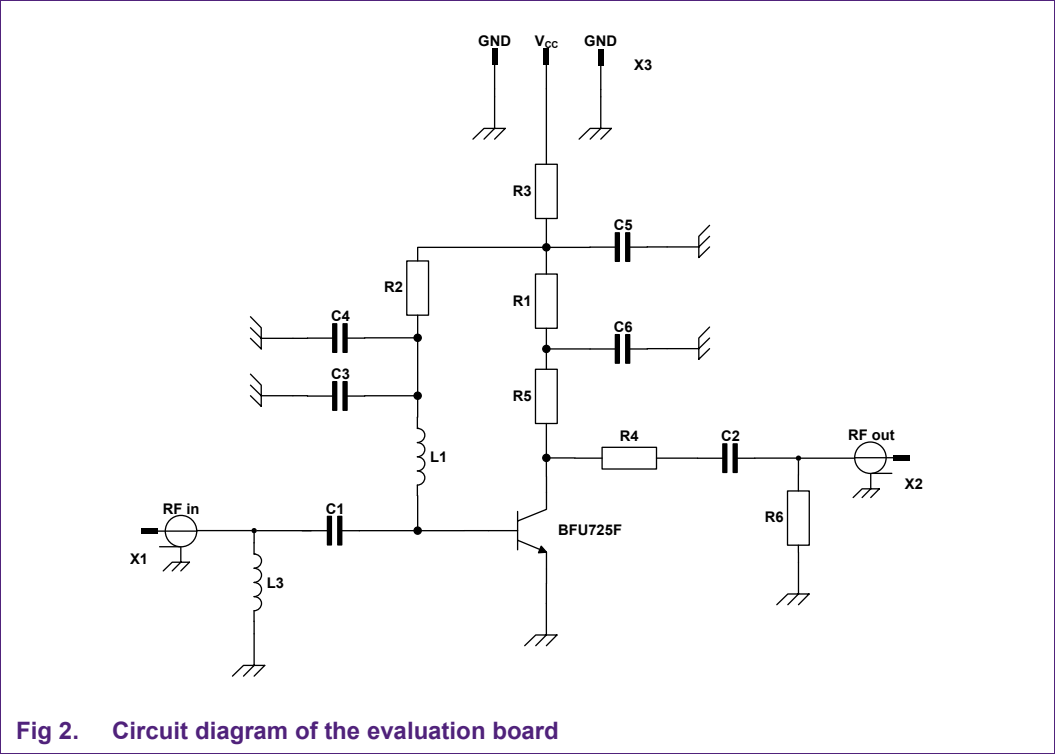


Fig 2. Circuit diagram of the evaluation board

3.2 Board Layout

Fig 3 shows the board layout with the components

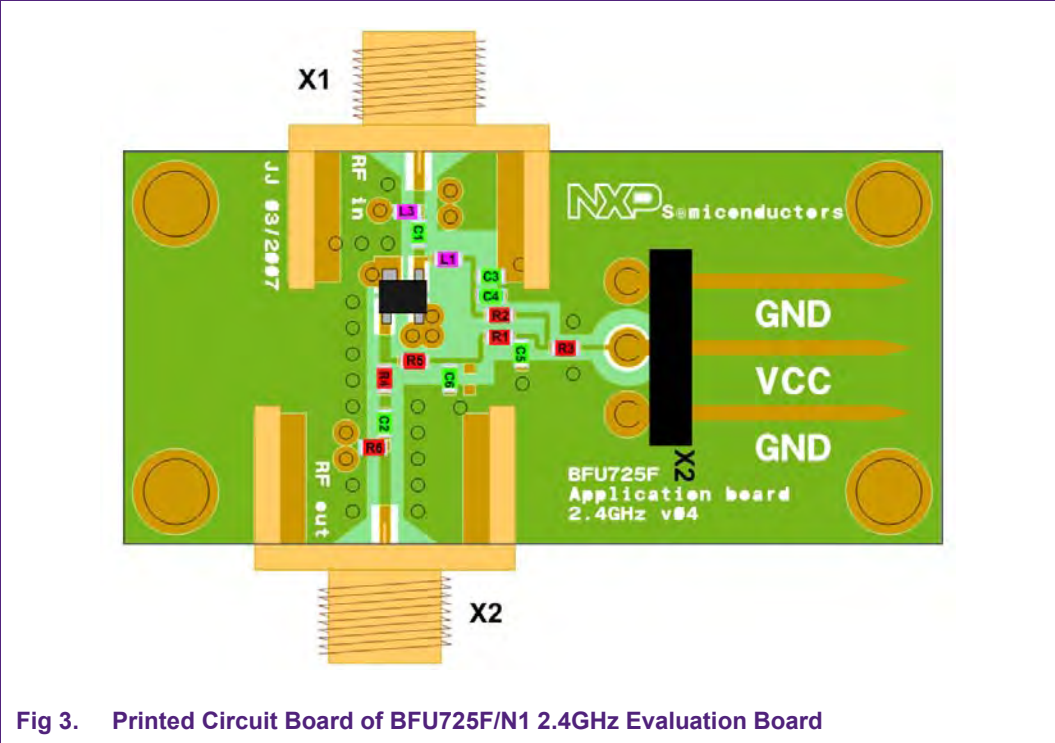
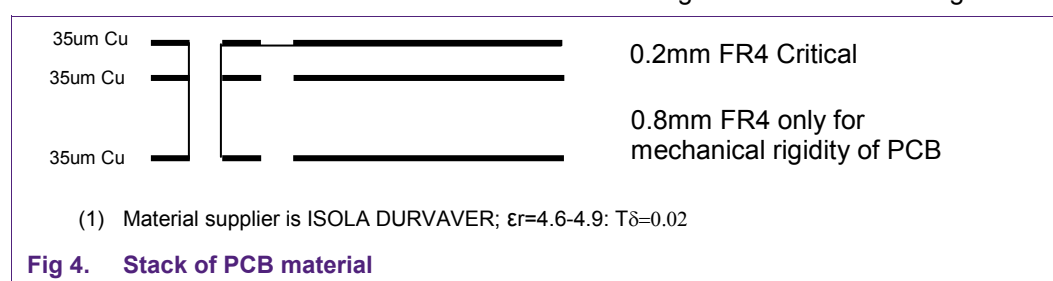


Fig 3. Printed Circuit Board of BBU725F/N1 2.4GHz Evaluation Board

### 3.3 PCB Layout

A good PCB Layout is an essential part of an RF circuit design. The EVB of the BFU725F/N1 can serve as a guideline for laying out a board using either the BFU725F/N1. Use controlled impedance lines for all high frequency inputs and outputs. Bypass VCC with decoupling capacitors, preferable located as close as possible to the device. For long bias lines it may be necessary to add decoupling capacitors along the line further away from the device. Proper grounding the emitters is also essential for the performance. Either connect the emitters directly to the ground plane or through vias, or do both.

The material that has been used for the EVB is FR4 using the stack shown in Fig 4.



### 3.4 Bill of Materials

**Table 4. Bill of Materials**

| Designator | Description      | Footprint | Value         | Supplier Name/type                                      | Comment                  |
|------------|------------------|-----------|---------------|---------------------------------------------------------|--------------------------|
| C1         | Capacitor        | 0402      | 15pF          | MurataGRM1555                                           | DC blocking *            |
| C2         | Capacitor        | 0402      | 2.7pF         | MurataGRM1555                                           | DC blocking *            |
| C3,C6      | Capacitor        | 0402      | 1.5pF         | MurataGRM1555                                           | LF Decoupling            |
| C4,C5      | Capacitor        | 0402      | 100nF         | MurataGRM1555                                           | LF Decoupling (optional) |
| L1         | Inductor         | 0402      | 12nH          | Murata/LQW15A High Q low Rs                             | Input matching           |
| L3         | Inductor         | 0402      | 5.6nH         | Murata/LQG15HS                                          | Input matching           |
| R1         | Resistor         | 0402      | 0 $\Omega$    | Various                                                 | Not used                 |
| R2         | Resistor         | 0402      | 51 k $\Omega$ | Various                                                 | Bias setting             |
| R3         | Resistor         | 0402      | 100 $\Omega$  | Various                                                 | Bias setting             |
| R4         | Resistor         | 0402      | 0 $\Omega$    | Various                                                 | Not Used                 |
| R5         | Resistor         | 0402      | 33 $\Omega$   | Various                                                 | Output matching          |
| R6         | Resistor         | 0402      | 27 $\Omega$   | Various                                                 | Output matching          |
| X1,X2      | SMA RF connector | -         |               | Johnson, End launch SMA 142-0701-841                    | RF input/ RF output      |
| X3         | DC header        | -         |               | Molex, PCB header, Right Angle, 1 row, 3 way 90121-0763 | Bias connector           |

## 4. Required Equipment

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In order to measure the evaluation board the following is necessary.

- ✓ DC Power Supply up to 30 mA at 3V.
- ✓ An RF Signal generator capable of generating an RF signal at the operating frequency of 2.4 GHz.
- ✓ An RF spectrum analyzer that covers at least the operating frequency of 2.4 GHz as well as a few of the harmonics, so up to 6 GHz should be sufficient.  
"Optional" a version with the capability of measuring noise figure is convenient.
- ✓ Amp meter to measure the supply current (optional).
- ✓ A Network analyzer for measuring gain, return loss and reverse Isolation.
- ✓ Noise figure analyzer.

## 5. Connections and Setup

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The BFU725F/N1 2.4GHz EVB is fully assembled and tested. Please follow the steps below for a step-by-step guide to operate the EVB and testing the device functions.

1. Connect the DC power supply set to 3V to the  $V_{CC}$  and GND terminals.
2. Connect the RF signal generator and the Spectrum Analyzer; to the RF input and the RF output of the EVB respectively. Do not turn on the RF output of the Signal generator yet, set it to -35dBm output power at 2.4GHz, set the spectrum analyzer on 2.4GHz center frequency and a reference level of 0dBm.
3. Turn on the DC power supply and it should read approximately 8 mA.
4. Enable the RF output of the generator; the Spectrum analyzer displays a tone of 2.4GHz at around -20dBm.
5. Instead of using a signal generator and spectrum analyzer one can also use a Network Analyzer NWA in order to measure Gain as well as in- and output return loss
6. For Noise figure evaluation, either a Noise-figure analyzer or a spectrum analyzer with noise option can be used. The use of a 5 dB noise source, like the Agilent 364B is recommended. When measuring the noise figure of the evaluation board, any kind of adaptors, cables etc between the noise source and the EVB should be avoided, since this affects the noise performance.

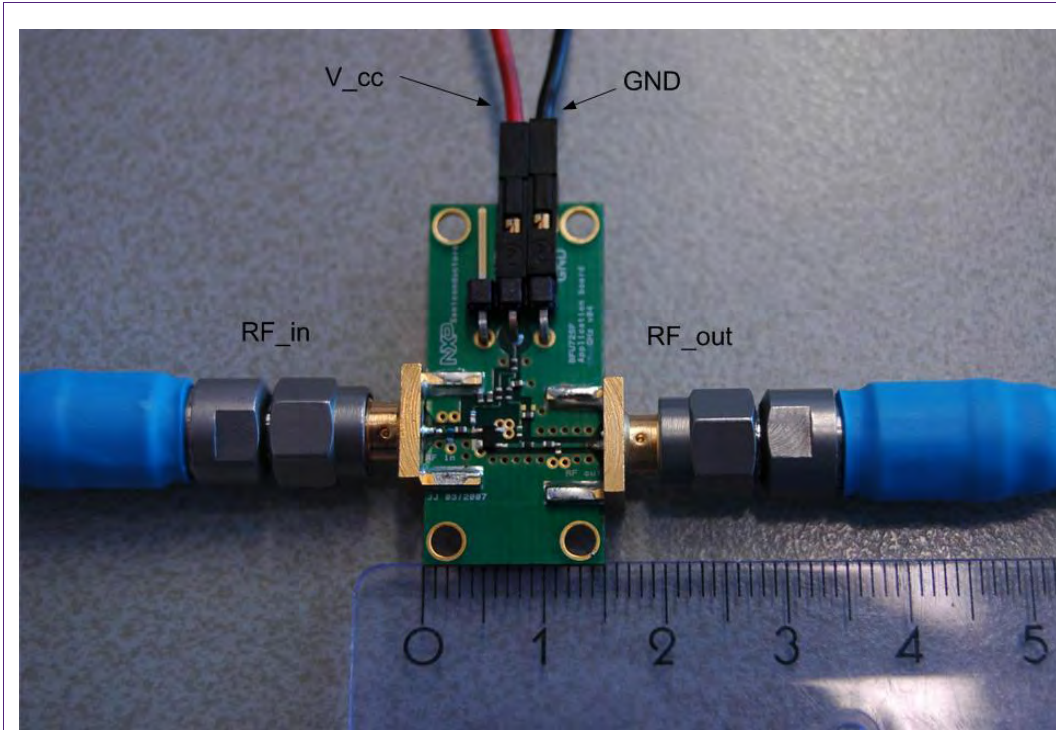


Fig 5. Evaluation board including its connections

6. Typical EVB Results

Table 5. Typical results measured on the evaluation board

| Parameter                          | Symbol             | BFU725F/N1 EVB | Unit | Comment |
|------------------------------------|--------------------|----------------|------|---------|
| Noise Figure                       | NF                 | 1.0            | dB   | [1]     |
| Power Gain                         | Gp                 | 15.3           | dB   |         |
| Input Return Loss                  | IRL                | 6.0            | dB   |         |
| Output Return Loss                 | ORL                | 7.2            | dB   |         |
| Reverse Isolation                  | ISO <sub>rev</sub> | 30.1           | dB   |         |
| Input 1dB Gain Compression         | IP1dB              | -23.0          | dBm  |         |
| Input 1dB Gain Compression         | OP1dB              | -8.7           | dBm  |         |
| Input third order intercept point  | IIP3               | -1.6           | dBm  |         |
| Output third order intercept point | OIP3               | 13.3           | dBm  |         |

[1] The noise figure and gain figures are measured at the SMA connectors of the evaluation board. The losses of the connectors and the PCB of approximately 0.1 dB are not subtracted.

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